

Keita Tachiki

List of Publications by Year in descending order

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papers

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1163065

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151

citing authors

#	ARTICLE	IF	CITATIONS
1	Body doping dependence of field-effect mobility in both n- and p-channel 4H-SiC metal-oxide-semiconductor field-effect transistors with nitrated gate oxides. Applied Physics Express, 2022, 15, 036503.	2.4	4
2	Mobility enhancement in heavily doped 4H-SiC (0001), (112̄,0), and (11̄,00) MOSFETs via an oxidation-minimizing process. Applied Physics Express, 2022, 15, 071001.	2.4	9
3	Mobility improvement of 4H-SiC (0001) MOSFETs by a three-step process of H₂ etching, SiO₂ deposition, and interface nitridation. Applied Physics Express, 2021, 14, 031001.	2.4	42
4	Improvement of Both n- and p-Channel Mobilities in 4H-SiC MOSFETs by High-Temperature N ₂ Annealing. IEEE Transactions on Electron Devices, 2021, 68, 638-644.	3.0	19
5	Short-Channel Effects in SiC MOSFETs Based on Analyses of Saturation Drain Current. IEEE Transactions on Electron Devices, 2021, 68, 1382-1384.	3.0	17
6	Design and formation of SiC (0001)/SiO₂ interfaces via Si deposition followed by low-temperature oxidation and high-temperature nitridation. Applied Physics Express, 2020, 13, 091003.	2.4	38
7	Formation of high-quality SiC(0001)/SiO₂ structures by excluding oxidation process with H₂ etching before SiO₂ deposition and high-temperature N₂ annealing. Applied Physics Express, 2020, 13, 121002.	2.4	25
8	Reduction of interface state density in SiC (0001) MOS structures by low-oxygen-partial-pressure annealing. Applied Physics Express, 2019, 12, 031001.	2.4	15
9	Estimation of Threshold Voltage in SiC Short-Channel MOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 3077-3080.	3.0	28